SILICON (Si) POWER MOSFET A CEM6368



CEM6368

60V A 37mΩ A 5.3A A Dual Si MOSFET

SILICON Si MOSFET A SMD type Dual N-channel enhancement mode UL94V-0 rated flame retardant epoxy SO8 package ▲ MSL 3 Super high dense cell density for extremely low R_{DS(ON)} High power and current handling capability

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MAXIMUM RATINGS

Parameter (T _A = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	60V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current	Ι _D	5.3A
Pulsed Drain Current Note 1	I _{DM}	21.2A
Maximum Power Dissipation	PD	2W
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +150°C

THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Ambient Note 2	R _{TH_JA}	62.5°C/W

APPLICATIONS

Audio	Battery Management	DC/DC	Industrial	Power
Amplifier	Systems	Converter	Control	Switches
()	+ -			

PIN DESCRIPTION

Circuit Diagram	Outline - Top View	Pin No.	Description
$\begin{array}{c} D_{1}(7,8) \\ \hline \\ G_{1}(2) \\ \hline \\ S_{1}(1) \end{array} \qquad \begin{array}{c} D_{2}(5,6) \\ \hline \\ G_{2}(4) \\ \hline \\ S_{2}(3) \end{array}$		1 2 3 4 5 6 7 8	Source MOSFET 1 Gate MOSFET 1 Source MOSFET 2 Gate MOSFET 2 Drain MOSFET 2 Drain MOSFET 2 Drain MOSFET 1 Drain MOSFET 1

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ELECTRICAL CHARACTERISTICS A T_A = 25°C, unless otherwise noted

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250\mu A$	BV _{DSS}	60			V
Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$	I _{DSS}			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I _{GSSF}			100	nA
Gate Body Leakage Current, Reverse	V_{GS} = -20V, V_{DS} = 0V	I _{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu A$	$V_{GS(th)}$	1		2.5	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_{D} = 5A$	R _{DS(ON)}		37	44	mΩ
Static Drain-Source On-Resistance	V_{GS} = 4.5V, I_{D} = 4A	R _{DS(ON)}		39	51	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	C _{ISS}		750		рF
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$	Coss		65		рF
Reverse Transfer Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	C _{RSS}		50		pF
Switching Characteristics Note 4						
Turn-On Delay Time	V_{DD} = 30V, V_{GS} = 10V, I_D = 6A, $R_{G(ext)}$ = 6 Ω	t _{D(ON)}		11		ns
Turn-On Rise Time	V_{DD} = 30V, V_{GS} = 10V, I_{D} = 6A, $R_{\text{G}(\text{ext})}$ = 6 Ω	t _R		4		ns
Turn-Off Delay Time	V_{DD} = 30V, V_{GS} = 10V, I_{D} = 6A, $R_{\text{G}(\text{ext})}$ = 6 Ω	t _{D(OFF)}		51		ns
Turn-Off Fall Time	V_{DD} = 30V, V_{GS} = 10V, I_{D} = 6A, $R_{\text{G}(\text{ext})}$ = 6 Ω	t _F		7		ns
Total Gate Charge	V_{DS} = 30V, V_{GS} = 4.5V, I_{D} = 4.5A	Q _G		9.7		nC
Gate Source Charge	V_{DS} = 30V, V_{GS} = 4.5V, I_D = 4.5A	Q _{GS}		1.6		nC
Gate Drain Charge	V_{DS} = 30V, V_{GS} = 4.5V, I_{D} = 4.5A	\mathbf{Q}_{GD}		4.2		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current ^{Note 2}		١ _s			1.5	А
Drain-Source Diode Forward Voltage ^{Note 3}	$V_{GS} = 0V$, $I_S = 1A$	V_{SD}			1.3	V

Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

2: Surface Mounted on FR4 Board, $t \le 10$ sec

3: Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

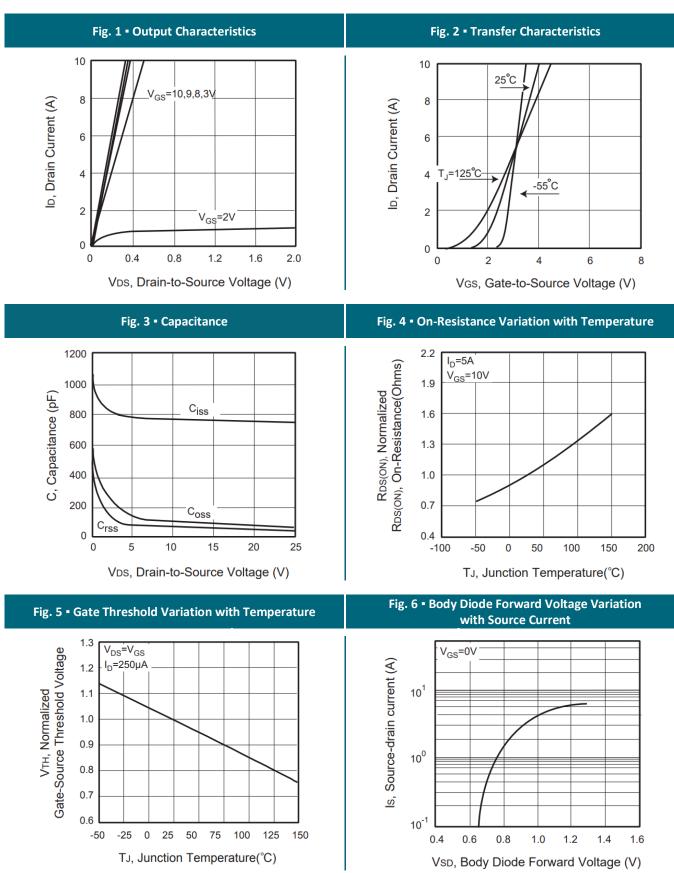
4: Guaranteed by design, not subject to production testing.



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REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE



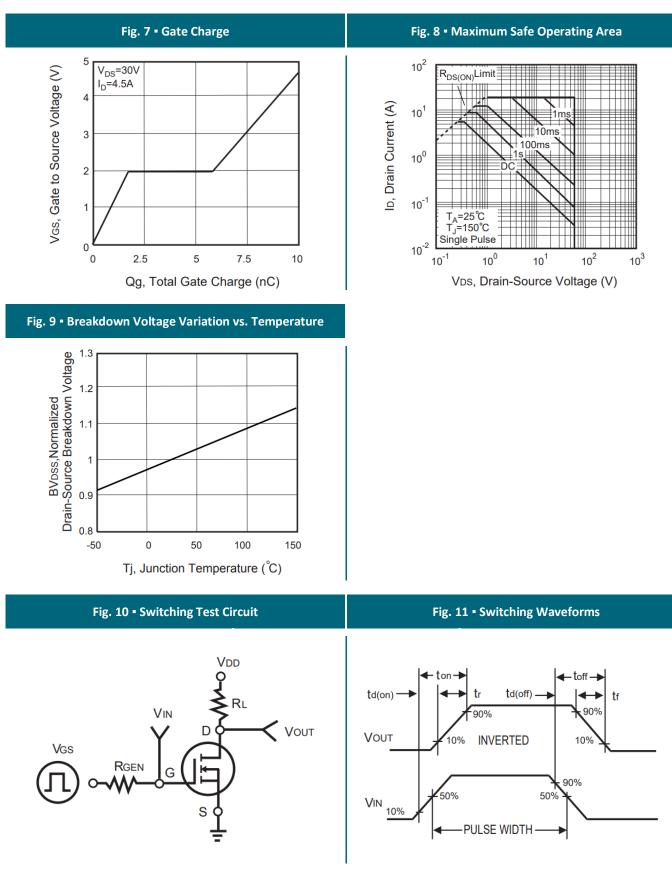
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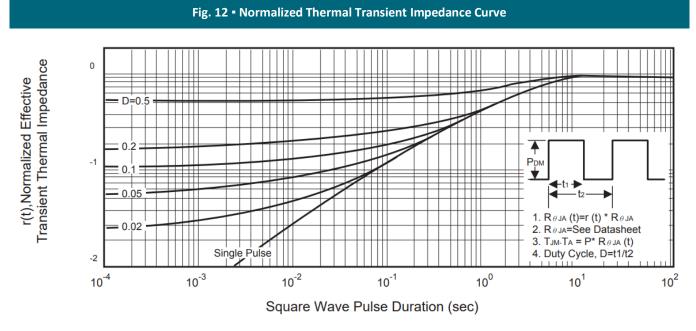
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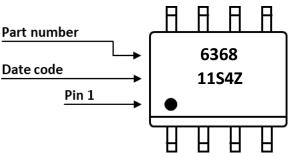


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REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE

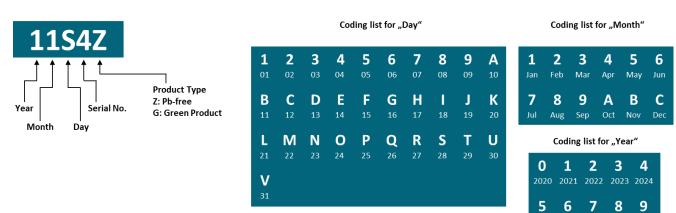


PART MARKING



DATE CODE

Example: 11S4Z

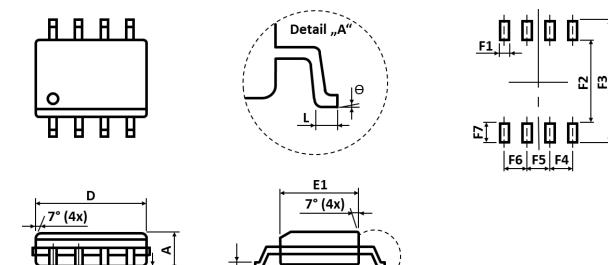


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• Detail "A"



PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	1.350	-	1.750	E1	3.700		4.060
A1	0.100	-	0.250	eB	5.800		6.200
В	0.310	-	0.510	е		1.270	
С	0.170	-	0.250	L	0.400		0.950
D	4.690	-	5.000	θ	0°	-	8°
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)

eВ

F1	-	0.500	-	F5	-	1.270
F2	-	4.250	-	F6	-	1.270
F3	-	6.250	-	F7	-	1.000
F4	-	1.270	-			

Notes:1. The suggested land pattern dimensions have been provided for reference only.2. For further information, please reference document IPC-7351A.

C

ORDERING INFORMATION

В

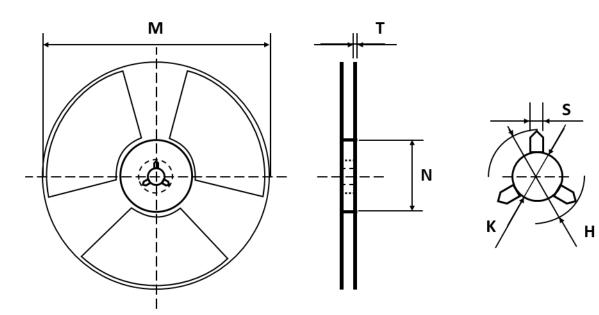
A1

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEM6368	SO8	13" Reel	2,500pcs	5,000pcs	40,000pcs



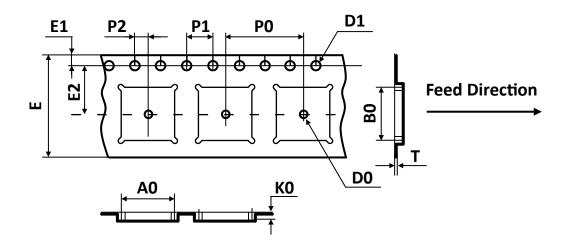


REEL DIMENSIONS All dimensions in mm



Tape Size	Reel Size	М	Ν	Т	Н	К	S
12mm	Ø330	Ø330.00	Ø100.00	2.20	20.00	13.20	3.00
1211111	\$550	±2.00	±0.50	±0.20	±1.00	±0.20	±1.00

TAPE DIMENSIONS All dimensions in mm



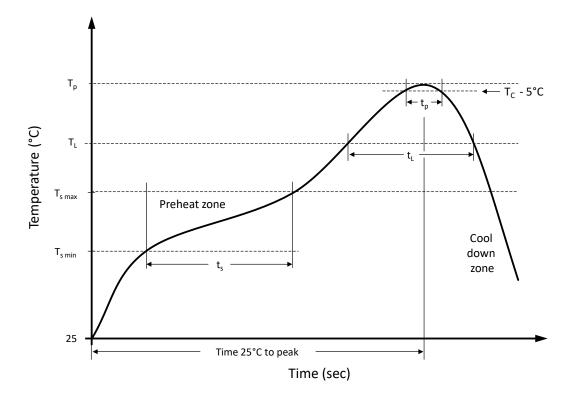
Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	т
SO8	6.50	5.30	2.05	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
308	±0.10	±0.10	±0.15	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.02

Note: All dimensions meet EIA-481-D requirements.





RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	T_{smin}	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time t_s from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T _L to T _p)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	ΤL	183 °C	217 °C
Time t_L maintained above T_L	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	tp	20 seconds max.	30 seconds max.
Ramp-down rate (T_L to T_p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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